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| APPLICATION NO.                    | FILING DATE  | FIRST NAMED INVENTOR | ATTORNEY DOCKET NO.     | CONFIRMATION NO |
|------------------------------------|--------------|----------------------|-------------------------|-----------------|
| 09/988,938                         | 02/01/2002   | Stephen J. Kovacic   | 115-01 US Div(2)        | 9218            |
| 25319 . 7                          | 05/06/2003   | •                    |                         |                 |
| FREEDMAN & ASSOCIATES              |              |                      | EXAMINER                |                 |
| 117 CENTREF<br>SUITE 350           | POINTE DRIVE | •                    | PHAM, THANH V           |                 |
| NEPEAN, ONTARIO, K2G 5X3<br>CANADA |              |                      | ART UNIT                | PAPER NUMBER    |
|                                    |              |                      | 2823                    |                 |
|                                    | •            |                      | DATE MAILED: 05/06/2003 |                 |

Please find below and/or attached an Office communication concerning this application or proceeding.

|   |  |  |   | SW.      |
|---|--|--|---|----------|
|   |  | Application No.  | Applicant(s)  |          |
|   |  | 09/988,938   | KOVACIC ET AL.  |          |
|   | Office Action Summary  | Examiner   | Art Unit  |          |
|   |  | Thanh V Pham   | 2823  |          |
| Period fo   | The MAILING DATE of this communication ap<br>or Reply  | pears on the cover sheet with  | the correspondence address  | ••       |
| THE I - External after - If the - If NC - Failu - Any I | ORTENED STATUTORY PERIOD FOR REPL MAILING DATE OF THIS COMMUNICATION. nsions of time may be available under the provisions of 37 CFR 1.1 SIX (6) MONTHS from the mailing date of this communication. period for reply specified above is less than thirty (30) days, a represent of the reply is specified above, the maximum statutory period reto reply within the set or extended period for reply will, by statute eply received by the Office later than three months after the mailing dispatent term adjustment. See 37 CFR 1.704(b). | 136(a). In no event, however, may a reply within the statutory minimum of thirty will apply and will expire SIX (6) MONTE, cause the application to become ABA | ly be timely filed  30) days will be considered timely.  IS from the mailing date of this communi | cation.  |
| 1)🖾   | Responsive to communication(s) filed on 31   | <u>March 2003</u> .  |   |          |
| 2a)⊠  | This action is <b>FINAL</b> . 2b) The  | nis action is non-final.   |   |          |
| 3) 🗌<br>Dispositi                                       | Since this application is in condition for allow closed in accordance with the practice under on of Claims   |  |   | rits is  |
| 4)🖂   | Claim(s) 10-16 and 22-32 is/are pending in the   | e application.   |   |          |
|   | 4a) Of the above claim(s) is/are withdra   | wn from consideration.   |   |          |
| 5)  | Claim(s) is/are allowed.   |  |   |          |
| 6)⊠   | Claim(s) 10-16 and 22-32 is/are rejected.  |  |   |          |
| 7)  | Claim(s) is/are objected to.   |  |   |          |
| 8)[   | Claim(s) are subject to restriction and/o  | or election requirement.   |   |          |
| Applicati   | on Papers  |  |   |          |
| 9) 🗌 .  | The specification is objected to by the Examine  | er.  |   |          |
| 10) 🔲 -   | Γhe drawing(s) filed on is/are: a)∏ acce   | pted or b)☐ objected to by the   | e Examiner.   |          |
|   | Applicant may not request that any objection to the  | e drawing(s) be held in abeyan   | ce. See 37 CFR 1.85(a).   |          |
| 11)[ ]  | Γhe proposed drawing correction filed on <u>31 Μ</u>   | <u>arch 2003</u> is: a)⊠ approved  | b) disapproved by the Exa   | miner.   |
|   | If approved, corrected drawings are required in re   | ply to this Office action.   |   |          |
| 12) 🔲 -   | The oath or declaration is objected to by the Ex   | caminer.   |   |          |
| Priority u  | nder 35 U.S.C. §§ 119 and 120  |  |   |          |
| 13)   | Acknowledgment is made of a claim for foreign  | n priority under 35 U.S.C. §   | 119(a)-(d) or (f).  |          |
| a)[   | ☐ All b) ☐ Some * c) ☐ None of:  |  |   |          |
|   | 1. Certified copies of the priority document   | s have been received.  |   |          |
|   | 2. Certified copies of the priority document   | s have been received in App  | olication No  |          |
| * S   | 3. Copies of the certified copies of the prio application from the International Buse the attached detailed Office action for a list   | reau (PCT Rule 17.2(a)).   | _   | ;        |
| 14)[] A   | cknowledgment is made of a claim for domest  | ic priority under 35 U.S.C. §  | 119(e) (to a provisional appli  | cation). |
|   | The translation of the foreign language process  |  |   |          |
| Attachmen   | •  | . ,  | -   |          |
| 2) Notic  | e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s)  | 5) Notice of Inf   | mmary (PTO-413) Paper No(s)<br>ormal Patent Application (PTO-152)                                 |          |
| I.S. Patent and Tr<br>PTO-326 (Re                       |  | ction Summary  | Part of Paper No. 8   |          |

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## **DETAILED ACTION**

- 1. The amended abstract of the disclosure is objected to because "The transistor device formed using the sacrificial mesa results in the base layer SiGe <u>from</u> being affected" should be--The transistor device formed using the sacrificial mesa results in the base layer SiGe <u>not</u> being affected--. Correction is required.
- 2. The disclosure is objected to under 37 CFR 1.71, as being so incomprehensible as to preclude a reasonable search of the prior art by the examiner. For example, the following item in the amended paragraph [0062] is not understood: "The term thickness is understood by those of skill in the art as a thickness of a layer in a direction perpendicular to a plane of a surface of a wafer on which the layer is formed". It is not always so, sometimes thin uniform thickness of a layer is applied in the horizontal intended direction.

Applicant is required to submit an amendment which clarifies the disclosure so that the examiner may make a proper comparison of the invention with the prior art.

Applicant should be careful not to introduce any new matter into the disclosure (i.e., matter which is not supported by the disclosure as originally filed).

- 3. The rejections are maintained as stated in the Office action mailed 12/31/02.
- 4. The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

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5. Claims 30-32 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

The term "controllable *thickness*" in claims 30-32 is a relative term which renders the claim indefinite. The term "controllable *thickness*" is not defined by the claim, the specification, *even amended*, does not provide a standard for ascertaining the requisite degree, and one of ordinary skill in the art would not be reasonably apprised of the scope of the invention. It is not clear *how much the* thickness is recited because it is not clear what is recited through use of "substantially reproducible *results*".

6. Claims 10-16 and 22-29 are rejected under 35 U.S.C. 102(a) as being anticipated by Yamazaki U.S. Patent No. 5,955,745.

The Yamazaki reference disclose a device comprising: a silicon substrate 23 forming one of a collector and an emitter (fig. 8), the substrate being of a first conductivity type (col. 9, lines 24-35); a layer of SiGe27 of a second conductivity type covering at least a portion of the silicon substrate; and a first layer of polysilicon 29 of the second conductivity type at least substantially supported by and covering a substantial portion of the SiGe layer with the exception of a window region, the layer of SiGe having its surface unaffected by a process of etching within the window region, the first layer of polysilicon forming a SiGe base terminal of the transistor; and, a second layer of polysilicon of the first conductivity type covering and contacting the unetched SiGe base of the transistor, said layer of polysilicon forming the other of the collector and the emitter.

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An insulating layer 30 separates the two layers of polysilicon.

- 7. The Affidavit under 37 CFR 1.132 filed 03/31/03 is insufficient to overcome the rejection of claims 10-16 and 22-29 based upon achieving a window region within the ptype polysilicon layer 29 as set forth in the last Office action because: Applicant's statement at page 2 that a timed etch is inherently etches the underlying layer is conclusory and not sufficiently probabative of the relevant issues to enable a reasonable trier of fact to determine that the statement is true.
- 8. Applicant's arguments filed 03/31/03 have been fully considered but they are not persuasive.

Applicants' arguments are based on figures 6a through 7b of '745. However, the rejections are based on the second embodiment of the Yamazaki reference which mainly concentrates on the complete single bi-polar transistor of fig. 8.

Applicants argue that patterning of layer 29 inherently affects layer 28. However, a timed etched stopping at the point of exposing layer 28 would leave layer 28 unaffected as recited. Note that figures 12A-12E do not show patterning of layer 28.

Applicants' claims are drawn to a single device and not an array of devices, a method of making a device or a method of making an array of devices.

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thanh V Pham whose telephone number is 703-308-2543. The examiner can normally be reached on M-T (6:30-5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone numbers

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for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7382 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

TvP May 2, 2003

George Fourson Primary Examiner